Product data sheet

1. General description

Hyperfast power diode in a SOD59 package.

2. Features and benefits

- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Half-bridge/full-bridge switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage			-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 133 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		-	-	5	А
Static characte	eristics						
V _F	forward voltage	I _F = 5 A; T _j = 25 °C; <u>Fig. 6</u>		-	2.5	3.3	V
		I _F = 5 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.4	2.1	V
Dynamic characteristics							
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	11	-	ns





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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode	}	001aaa020
mb	mb	mounting base; connected to cathode	TO-220AC (SOD59)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BYC5-600P	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59			

7. Marking

Table 4. Marking codes

Type number	Marking code
BYC5-600P	BYC5-600P

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 133 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	5	A
I _{FRM}	repetitive peak forward current	$δ$ = 0.5; t_p = 25 μs; T_{mb} ≤ 133 °C; square-wave pulse	-	10	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	60	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	65	Α
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

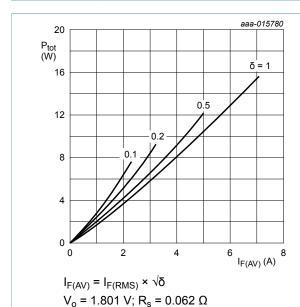


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

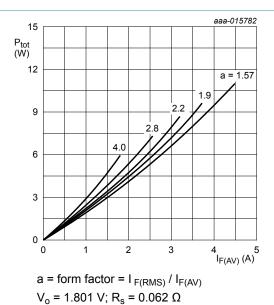


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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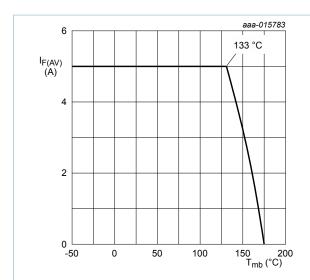


Fig. 3. Forward current as a function of mounting base temperature; maximum values

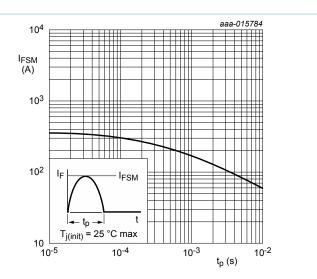


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	3.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

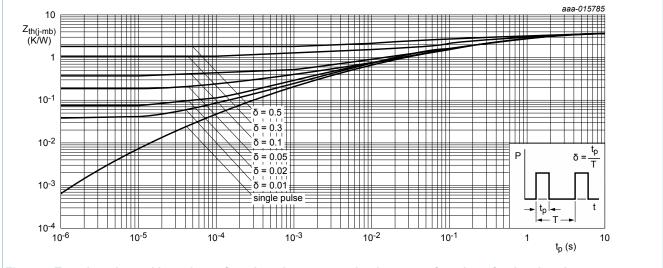


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

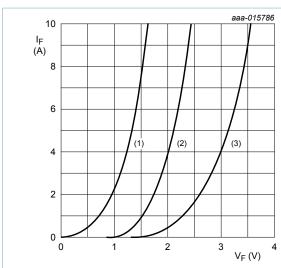
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _F	forward voltage	I _F = 5 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.5	3.3	V
		I _F = 5 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.4	2.1	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	0.6	mA
Dynamic ch	naracteristics		'			
Q _r recovered charge	recovered charge	$I_F = 5 \text{ A}$; $V_R = 200 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	19	-	nC
	$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	45	-	nC	
t _{rr} revers	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	11	-	ns
		$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	23	-	ns
		$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	28	-	ns
		$I_F = 5 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	13	25	ns
	peak reverse recovery current	$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	1.7	-	Α
		I _F = 5 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _j = 125 °C; <u>Fig. 7</u>	-	3.2	-	Α

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 V_o = 1.801 V; R_s = 0.062 Ω

(1) T_j = 150 °C; typical values

(2) T_j = 150 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage

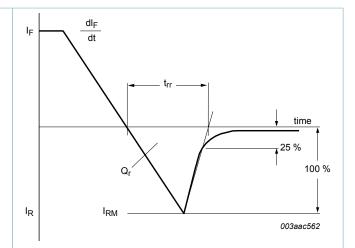
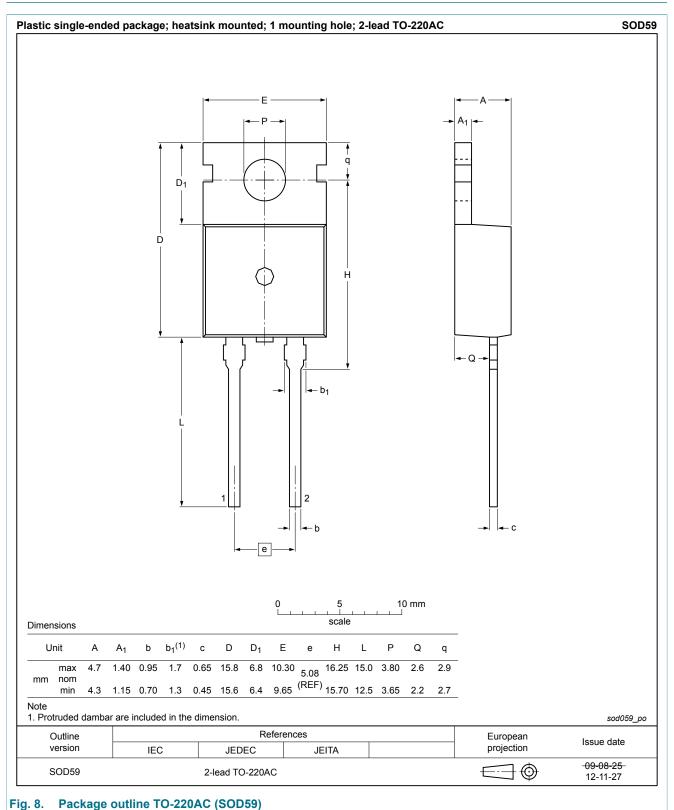


Fig. 7. Reverse recovery definitions; ramp recovery

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11. Package outline



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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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